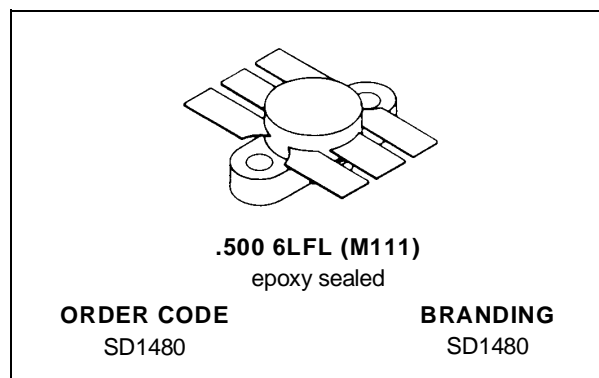
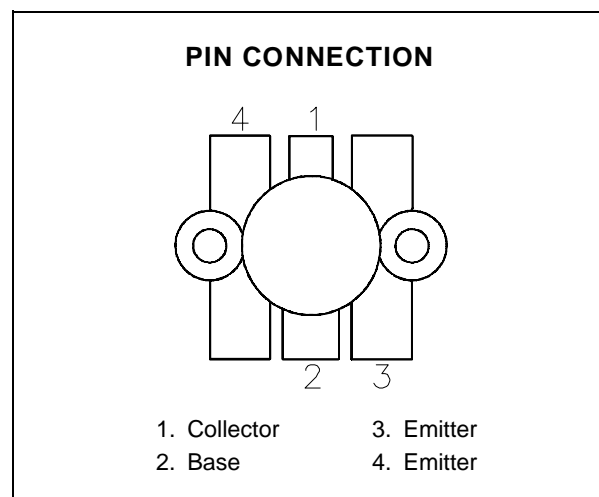


**RF & MICROWAVE TRANSISTORS
 VHF APPLICATIONS**

- 136 - 175 MHz
- 28 VOLTS
- EFFICIENCY 55%
- COMMON EMITTER
- GOLD METALLIZATION
- INTERNAL INPUT MATCHING
- $P_{OUT} = 125 \text{ W MIN. WITH } 9.2 \text{ dB GAIN}$


DESCRIPTION

The SD1480 is a common emitter 28 V Class C epitaxial silicon NPN planar transistor designed primarily for VHF communications applications. This internally matched device incorporates diffused emitter ballasting resistors and provides high gain and stable operation across the entire 136 - 175 MHz VHF communications band.


ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	65	V
V_{CEO}	Collector-Emitter Voltage	36	V
V_{CES}	Collector-Emitter Voltage	65	V
V_{EBO}	Emitter-Base Voltage	4.0	V
I_C	Device Current	20	A
P_{DISS}	Power Dissipation	270	W
T_J	Junction Temperature	+200	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	- 65 to +150	$^{\circ}\text{C}$

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance	0.65	$^{\circ}\text{C/W}$
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SD1480

ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

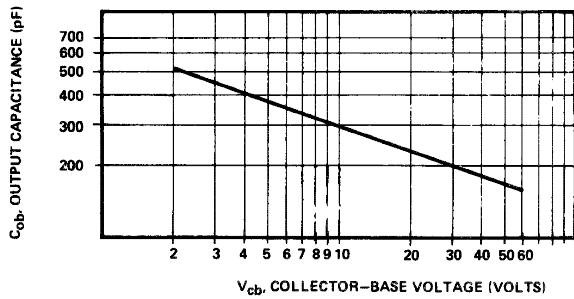
Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV _{CBO}	I _C = 100 mA	I _E = 0 mA	65	—	—	V
BV _{CES}	I _C = 100 mA	V _{BE} = 0 V	65	—	—	V
BV _{CEO}	I _C = 100 mA	I _B = 0 mA	35	—	—	V
BV _{EBO}	I _E = 10 mA	I _C = 0 mA	4.0	—	—	V
I _{CES}	V _{CE} = 30 V	I _E = 0 mA	—	—	15	mA
h _{FE}	V _{CE} = 5 V	I _C = 5 A	20	—	200	—

DYNAMIC

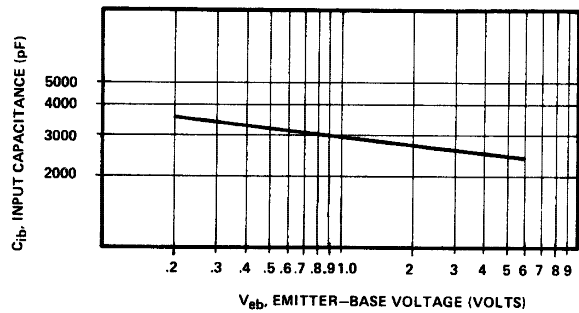
Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P _{OUT}	f = 150 MHz	P _{IN} = 15 W	V _{CE} = 28 V	125	—	—	W
P _G	f = 150 MHz	P _{OUT} = 125 W	V _{CE} = 28 V	9.2	—	—	dB
η _c	f = 150 MHz	P _{OUT} = 125 W	V _{CE} = 28 V	55	—	—	%
C _{OB}	f = 1 MHz	V _{CB} = 28 V		—	—	250	pF
Load Mismatch	f = 150 MHz	P _{IN} = 15 W	V _{CE} = 28 V	20:1	—	—	VSWR

TYPICAL PERFORMANCE

OUTPUT CAPACITANCE vs COLLECTOR BASE VOLTAGE

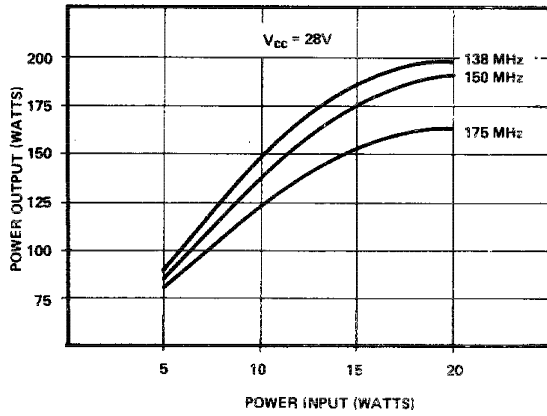


INPUT CAPACITANCE vs EMITTER BASE VOLTAGE

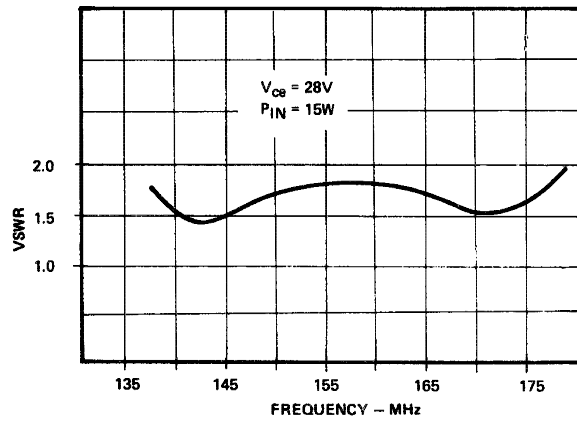


TYPICAL PERFORMANCE (cont'd)

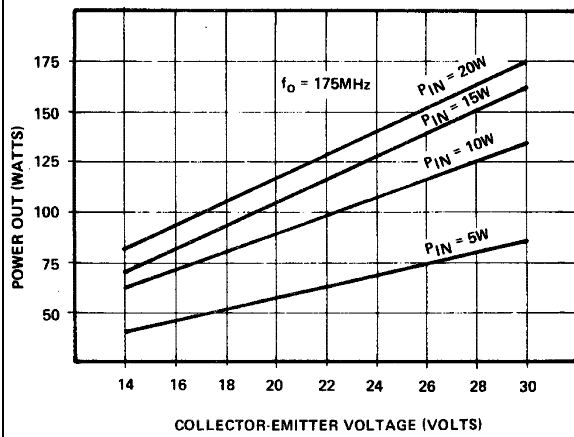
POWER OUTPUT vs POWER INPUT



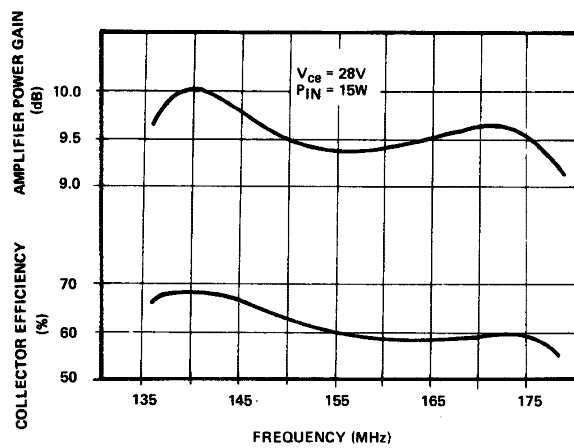
INPUT VSWR vs FREQUENCY



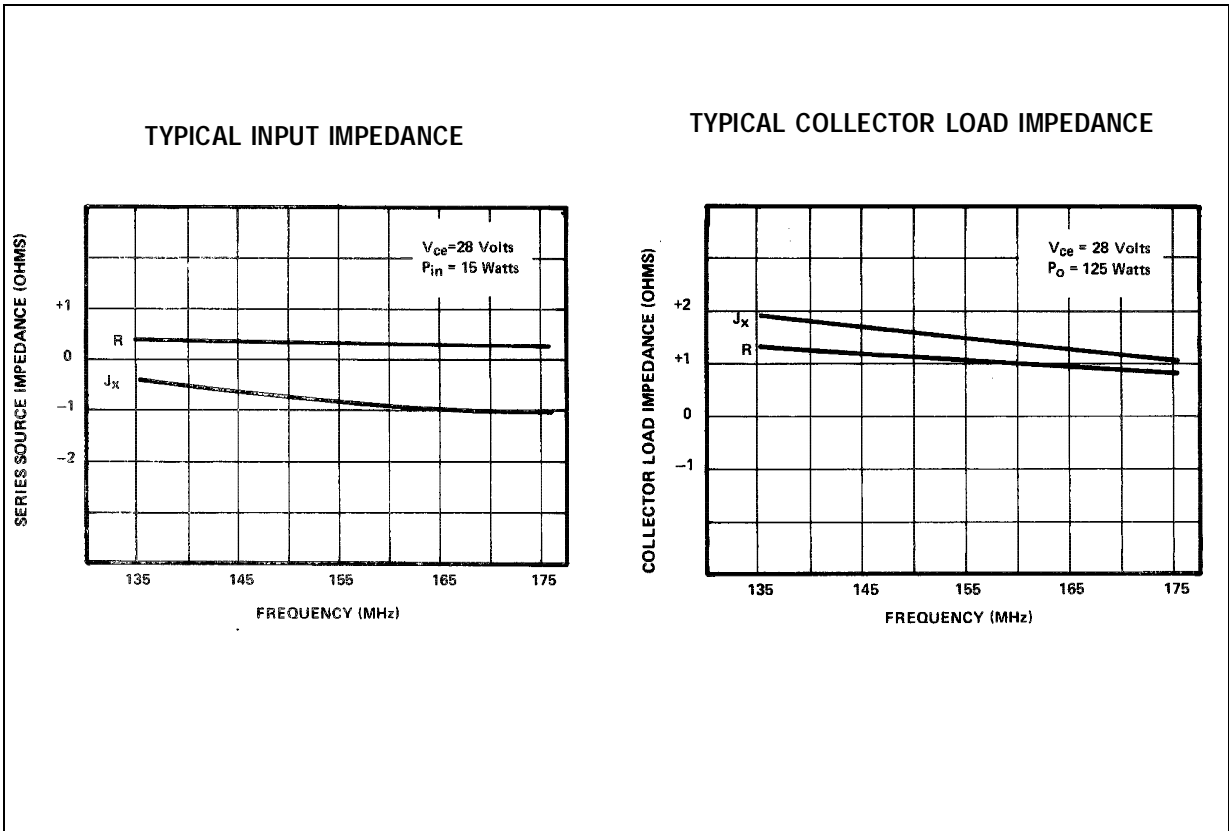
POWER OUTPUT vs COLLECTOR EMITTER VOLTAGE



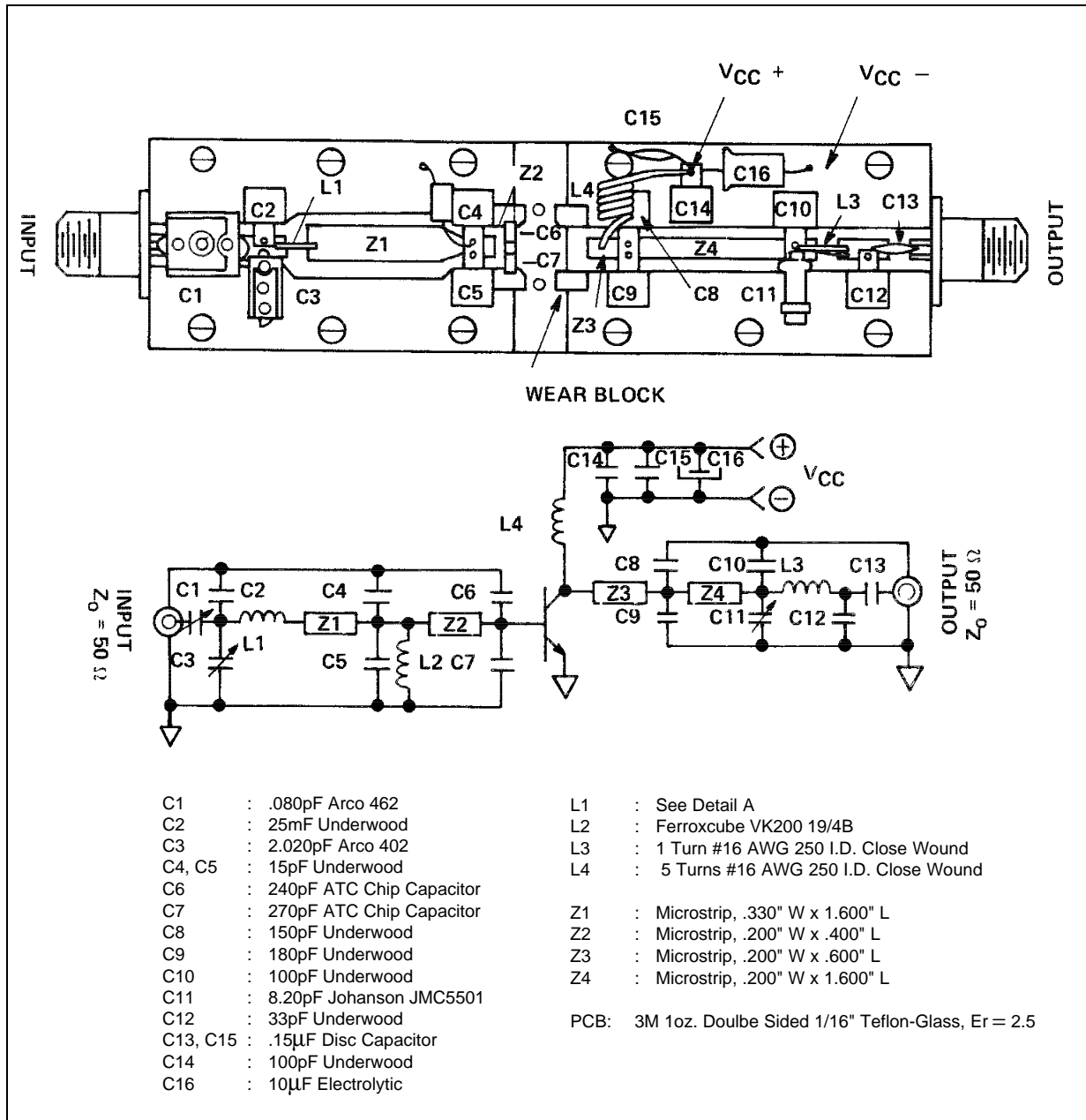
POWER GAIN & COLLECTOR EFFICIENCY vs FREQUENCY



IMPEDANCE DATA

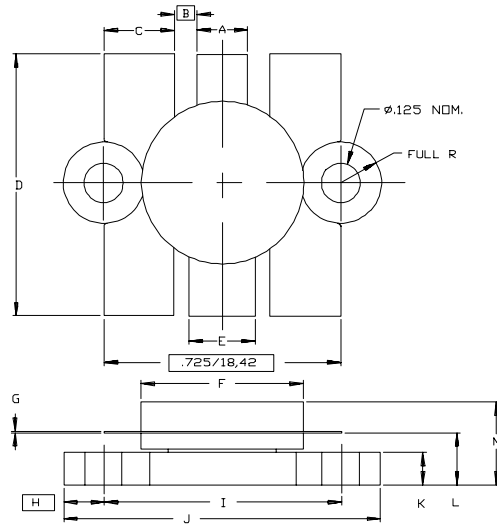


TEST CIRCUIT



PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0111 rev. D



SGS-THOMSON MICROELECTRONICS		CONT'D			
	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.150/3.43	.160/4.06	K	.095/2.41	.105/2.67
B	.045/1.14		L	.160/4.06	.180/4.58
C	.210/5.33	.220/5.59	M		.285/7.24
D	.835/21.21	.865/21.97			
E	.200/5.08	.210/5.33			
F	.490/12.45	.510/12.95			
G	.003/0.08	.007/0.18			
H	.125/3.18				
I	.720/18.29	.730/18.54			
J	.970/24.64	.980/24.89			

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